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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	STM8
Core Size	8-Bit
Speed	24MHz
Connectivity	I²C, IrDA, LINbus, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, POR, PWM, WDT
Number of I/O	34
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	1K x 8
RAM Size	6K x 8
Voltage - Supply (Vcc/Vdd)	2.95V ~ 5.5V
Data Converters	A/D 9x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	44-LQFP
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm8s207s6t6c

1 Introduction

This datasheet contains the description of the STM8S20xxx features, pinout, electrical characteristics, mechanical data and ordering information.

- For complete information on the STM8S microcontroller memory, registers and peripherals, please refer to the STM8S microcontroller family reference manual (RM0016).
- For information on programming, erasing and protection of the internal Flash memory please refer to the STM8S Flash programming manual (PM0051).
- For information on the debug and SWIM (single wire interface module) refer to the STM8 SWIM communication protocol and debug module user manual (UM0470).
- For information on the STM8 core, please refer to the STM8 CPU programming manual (PM0044).

2 Description

The STM8S20xxx performance line 8-bit microcontrollers offer from 32 to 128 Kbytes Flash program memory. They are referred to as high-density devices in the STM8S microcontroller family reference manual.

All STM8S20xxx devices provide the following benefits: reduced system cost, performance robustness, short development cycles, and product longevity.

The system cost is reduced thanks to an integrated true data EEPROM for up to 300 k write/erase cycles and a high system integration level with internal clock oscillators, watchdog, and brown-out reset.

Device performance is ensured by 20 MIPS at 24 MHz CPU clock frequency and enhanced characteristics which include robust I/O, independent watchdogs (with a separate clock source), and a clock security system.

Short development cycles are guaranteed due to application scalability across a common family product architecture with compatible pinout, memory map and modular peripherals. Full documentation is offered with a wide choice of development tools.

Product longevity is ensured in the STM8S family thanks to their advanced core which is made in a state-of-the art technology for applications with 2.95 V to 5.5 V operating supply.

Asynchronous communication (UART mode)

- Full duplex communication - NRZ standard format (mark/space)
- Programmable transmit and receive baud rates up to 1 Mbit/s (f_{CPU}/16) and capable of following any standard baud rate regardless of the input frequency
- Separate enable bits for transmitter and receiver
- Two receiver wakeup modes:
  - Address bit (MSB)
  - Idle line (interrupt)
- Transmission error detection with interrupt generation
- Parity control

LIN master capability

- Emission: Generates 13-bit sync break frame
- Reception: Detects 11-bit break frame

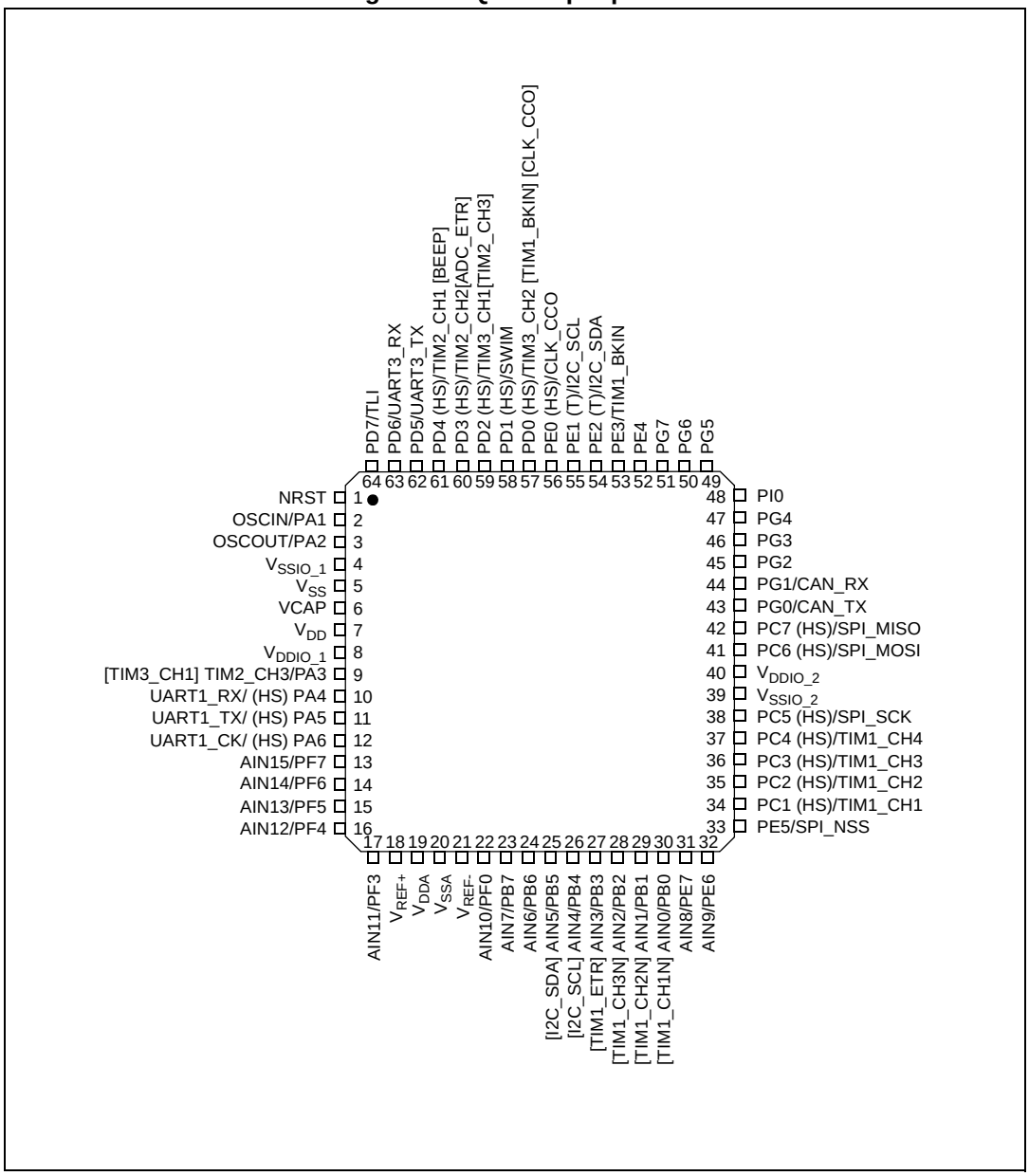
LIN slave mode

- Autonomous header handling - one single interrupt per valid message header
- Automatic baud rate synchronization - maximum tolerated initial clock deviation ±15%
- Sync delimiter checking
- 11-bit LIN sync break detection - break detection always active
- Parity check on the LIN identifier field
- LIN error management
- Hot plugging support

4.14.3 SPI

- Maximum speed: 10 Mbit/s (f_{MASTER}/2) both for master and slave
- Full duplex synchronous transfers
- Simplex synchronous transfers on two lines with a possible bidirectional data line
- Master or slave operation - selectable by hardware or software
- CRC calculation
- 1 byte Tx and Rx buffer
- Slave/master selection input pin

Figure 4. LQFP 64-pin pinout



1. (HS) high sink capability.
2. (T) True open drain (P-buffer and protection diode to V_{DD} not implemented).
3. [ ] alternate function remapping option (If the same alternate function is shown twice, it indicates an exclusive choice not a duplication of the function).
4. CAN_RX and CAN_TX is available on STM8S208xx devices only.

Table 5. Legend/abbreviations for pinout table

Type	I= Input, O = Output, S = Power supply	
Level	Input	CM = CMOS
	Output	HS = High sink
Output speed	O1 = Slow (up to 2 MHz) O2 = Fast (up to 10 MHz) O3 = Fast/slow programmability with slow as default state after reset O4 = Fast/slow programmability with fast as default state after reset	
Port and control configuration	Input	float = floating, wpu = weak pull-up
	Output	T = True open drain, OD = Open drain, PP = Push pull
Reset state	Bold **X** (pin state after internal reset release) Unless otherwise specified, the pin state is the same during the reset phase and after the internal reset release.	

Table 6. Pin description

Pin number					Pin name	Type	Input			Output				Main function (after reset)	Default alternate function	Alternate function after remap [option bit]
LQFP80	LQFP64	LQFP48	LQFP44	LQFP32			floating	wpu	Ext. interrupt	High sink	Speed	OD	PP			
1	1	1	1	1	NRST	I/O		**X**						Reset		
2	2	2	2	2	PA1/OSCIN	I/O	**X**	X			O1	X	X	**Port A1**	Resonator/ crystal in	
3	3	3	3	3	PA2/OSCOUT	I/O	**X**	X	X		O1	X	X	**Port A2**	Resonator/ crystal out	
4	4	4	4	-	V_{SSIO_1}	S								I/O ground		
5	5	5	5	4	V_{SS}	S								Digital ground		
6	6	6	6	5	VCAP	S								1.8 V regulator capacitor		
7	7	7	7	6	V_{DD}	S								Digital power supply		
8	8	8	8	7	V_{DDIO_1}	S								I/O power supply		
9	9	9	-	-	PA3/TIM2_CH3	I/O	**X**	X	X		O1	X	X	**Port A3**	Timer 2 - channel3	TIM3_CH1 [AFR1]
10	10	10	9	-	PA4/UART1_RX (1)	I/O	**X**	X	X	HS	O3	X	X	**Port A4**	UART1 receive	
11	11	11	10	-	PA5/UART1_TX	I/O	**X**	X	X	HS	O3	X	X	**Port A5**	UART1 transmit	

Table 13. Option byte description (continued)

Option byte no.	Description
OPTBL	**BL[7:0]** *Bootloader option byte* For STM8S products, this option is checked by the boot ROM code after reset. Depending on the content of addresses 0x487E, 0x487F, and 0x8000 (reset vector), the CPU jumps to the bootloader or to the reset vector. Refer to the UM0560 (STM8L/S bootloader manual) for more details. For STM8L products, the bootloader option bytes are on addresses 0xXXXX and 0xXXXX+1 (2 bytes). These option bytes control whether the bootloader is active or not. For more details, refer to the UM0560 (STM8L/S bootloader manual) for more details.

Total current consumption in wait mode

Table 22. Total current consumption in wait mode at V_{DD} = 5 V

Symbol	Parameter	Conditions		Typ	Max(1)	Unit
$I_{DD(WFI)}$	Supply current in wait mode	$f_{CPU} = f_{MASTER}$ = 24 MHz, $T_A \leq$ 105 °C	HSE crystal osc. (24 MHz)	2.4		mA
			HSE user ext. clock (24 MHz)	1.8	4.7	
		$f_{CPU} = f_{MASTER}$ = 16 MHz	HSE crystal osc. (16 MHz)	2.0		
			HSE user ext. clock (16 MHz)	1.4	4.4	
			HSI RC osc. (16 MHz)	1.2	1.6	
		$f_{CPU} = f_{MASTER}/128$ = 125 kHz	HSI RC osc. (16 MHz)	1.0		
		$f_{CPU} = f_{MASTER}/128$ = 15.625 kHz	HSI RC osc. (16 MHz/8)(2)	0.55		
		$f_{CPU} = f_{MASTER}$ = 128 kHz	LSI RC osc. (128 kHz)	0.5		

1. Data based on characterization results, not tested in production.
2. Default clock configuration measured with all peripherals off.

Table 23. Total current consumption in wait mode at V_{DD} = 3.3 V

Symbol	Parameter	Conditions		Typ	Max(1)	Unit
$I_{DD(WFI)}$	Supply current in wait mode	$f_{CPU} = f_{MASTER}$ = 24 MHz, $T_A \leq$ 105 °C	HSE crystal osc. (24 MHz)	2.0		mA
			HSE user ext. clock (24 MHz)	1.8	4.7	
		$f_{CPU} = f_{MASTER}$ = 16 MHz	HSE crystal osc. (16 MHz)	1.6		
			HSE user ext. clock (16 MHz)	1.4	4.4	
			HSI RC osc. (16 MHz)	1.2	1.6	
		$f_{CPU} = f_{MASTER}/128$ = 125 kHz	HSI RC osc. (16 MHz)	1.0		
		$f_{CPU} = f_{MASTER}/128$ = 15.625 kHz	HSI RC osc. (16 MHz/8)(2)	0.55		
		$f_{CPU} = f_{MASTER}/128$ = 15.625 kHz	LSI RC osc. (128 kHz)	0.5		

1. Data based on characterization results, not tested in production.
2. Default clock configuration measured with all peripherals off.

10.3.3 External clock sources and timing characteristics

HSE user external clock

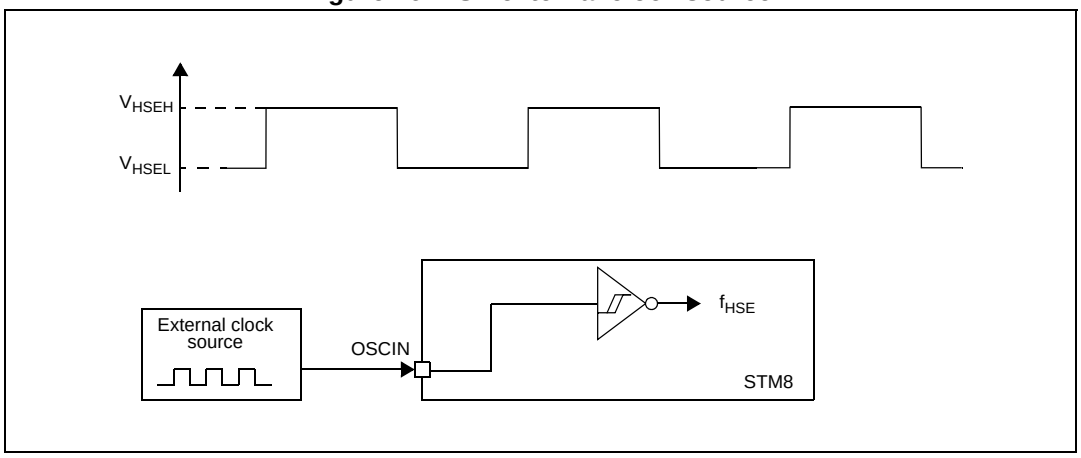
Subject to general operating conditions for V_{DD} and T_A.

Table 31. HSE user external clock characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSE_ext}	User external clock source frequency		0		24	MHz
V_{HSEH}(1)	OSCIN input pin high level voltage		0.7 x V_{DD}		V_{DD} + 0.3 V	V
V_{HSEL}(1)	OSCIN input pin low level voltage		V_{SS}		0.3 x V_{DD}	
I_{LEAK_HSE}	OSCIN input leakage current	$V_{SS} < V_{IN} < V_{DD}$	-1		1	µA

1. Data based on characterization results, not tested in production.

Figure 16. HSE external clock source



HSE crystal/ceramic resonator oscillator

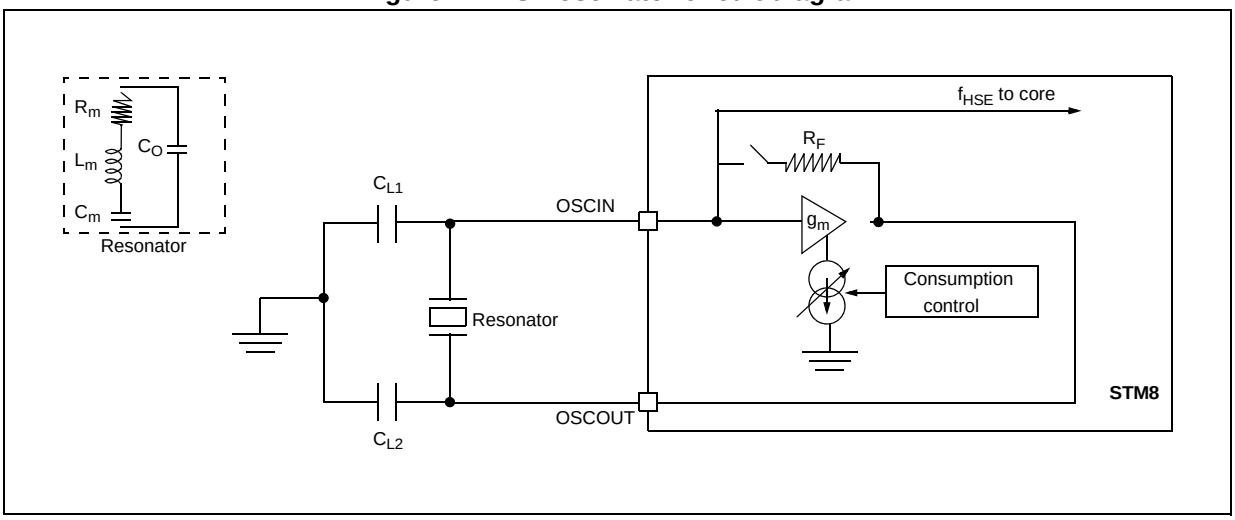
The HSE clock can be supplied with a 1 to 24 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph is based on characterization results with specified typical external components. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and start-up stabilization time. Refer to the crystal resonator manufacturer for more details (frequency, package, accuracy...).

Table 32. HSE oscillator characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSE}	External high speed oscillator frequency		1		24	MHz
R_F	Feedback resistor			220		kΩ
$C^{(1)}$	Recommended load capacitance (2)				20	pF
$I_{DD(HSE)}$	HSE oscillator power consumption	C = 20 pF, f_{OSC} = 24 MHz			6 (startup) 2 (stabilized)(3)	mA
		C = 10 pF, f_{OSC} = 24 MHz			6 (startup) 1.5 (stabilized)(3)	
g_m	Oscillator transconductance		5			mA/V
$t_{SU(HSE)}^{(4)}$	Startup time	V_{DD} is stabilized		1		ms

1. C is approximately equivalent to 2 x crystal Cload.
2. The oscillator selection can be optimized in terms of supply current using a high quality resonator with small R_m value. Refer to crystal manufacturer for more details
3. Data based on characterization results, not tested in production.
4. $t_{SU(HSE)}$ is the start-up time measured from the moment it is enabled (by software) to a stabilized 24 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

Figure 17. HSE oscillator circuit diagram

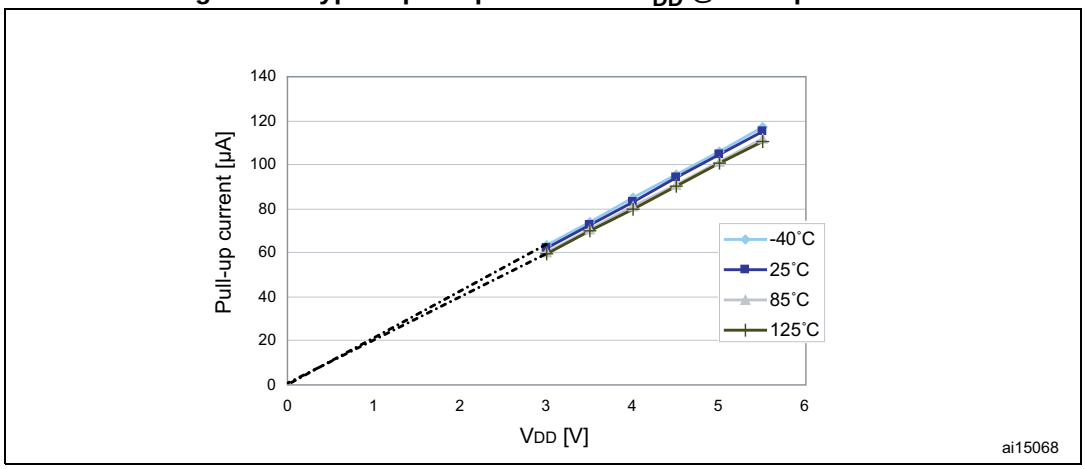


HSE oscillator critical g_m formula

$$g_{mcrit} = (2 \times \Pi \times f_{HSE})^2 \times R_m(2Co + C)^2$$

R_m: Notional resistance (see crystal specification)
L_m: Notional inductance (see crystal specification)
C_m: Notional capacitance (see crystal specification)
Co: Shunt capacitance (see crystal specification)
C_{L1}=C_{L2}=C: Grounded external capacitance
$g_m >> g_{mcrit}$

Figure 22. Typical pull-up current vs V_{DD} @ 4 temperatures



1. The pull-up is a pure resistor (slope goes through 0).

Table 38. Output driving current (standard ports)

Symbol	Parameter	Conditions	Min	Max	Unit
V_{OL}	Output low level with 8 pins sunk	I_{IO} = 10 mA, V_{DD} = 5 V		2	V
	Output low level with 4 pins sunk	I_{IO} = 4 mA, V_{DD} = 3.3 V		1(1)	
V_{OH}	Output high level with 8 pins sourced	I_{IO} = 10 mA, V_{DD} = 5 V	2.8		V
	Output high level with 4 pins sourced	I_{IO} = 4 mA, V_{DD} = 3.3 V	2.1(1)		

1. Data based on characterization results, not tested in production

Table 39. Output driving current (true open drain ports)

Symbol	Parameter	Conditions	Max	Unit
V_{OL}	Output low level with 2 pins sunk	I_{IO} = 10 mA, V_{DD} = 5 V	1	V
		I_{IO} = 10 mA, V_{DD} = 3.3 V	1.5(1)	
		I_{IO} = 20 mA, V_{DD} = 5 V	2(1)	

1. Data based on characterization results, not tested in production

Table 40. Output driving current (high sink ports)

Symbol	Parameter	Conditions	Min	Max	Unit
V_{OL}	Output low level with 8 pins sunk	I_{IO} = 10 mA, V_{DD} = 5 V		0.8	V
	Output low level with 4 pins sunk	I_{IO} = 10 mA, V_{DD} = 3.3 V		1(1)	
	Output low level with 4 pins sunk	I_{IO} = 20 mA, V_{DD} = 5 V		1.5(1)	
V_{OH}	Output high level with 8 pins sourced	I_{IO} = 10 mA, V_{DD} = 5 V	4.0		
	Output high level with 4 pins sourced	I_{IO} = 10 mA, V_{DD} = 3.3 V	2.1(1)		
	Output high level with 4 pins sourced	I_{IO} = 20 mA, V_{DD} = 5 V	3.3(1)		

1. Data based on characterization results, not tested in production

Figure 31. Typ. V_{DD} - V_{OH} @ V_{DD} = 5 V (high sink ports)

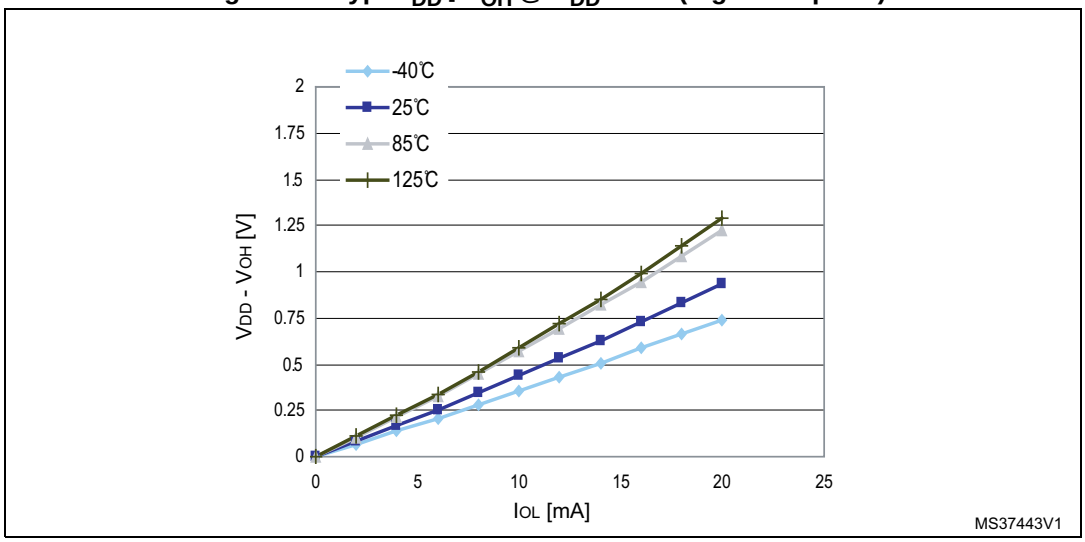


Figure 32. Typ. V_{DD} - V_{OH} @ V_{DD} = 3.3 V (high sink ports)

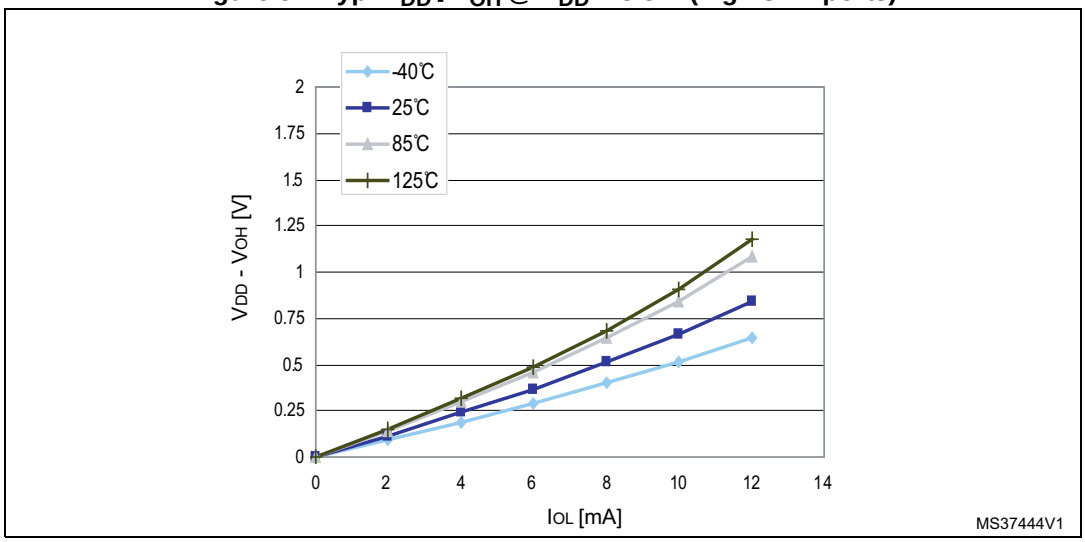


Figure 34. Typical NRST pull-up resistance vs V_{DD} @ 4 temperatures

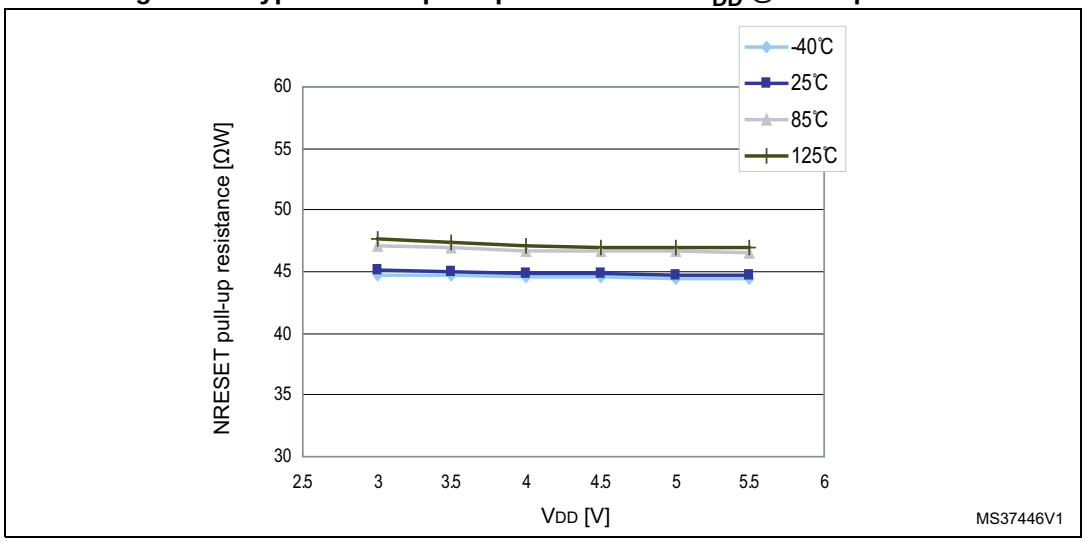
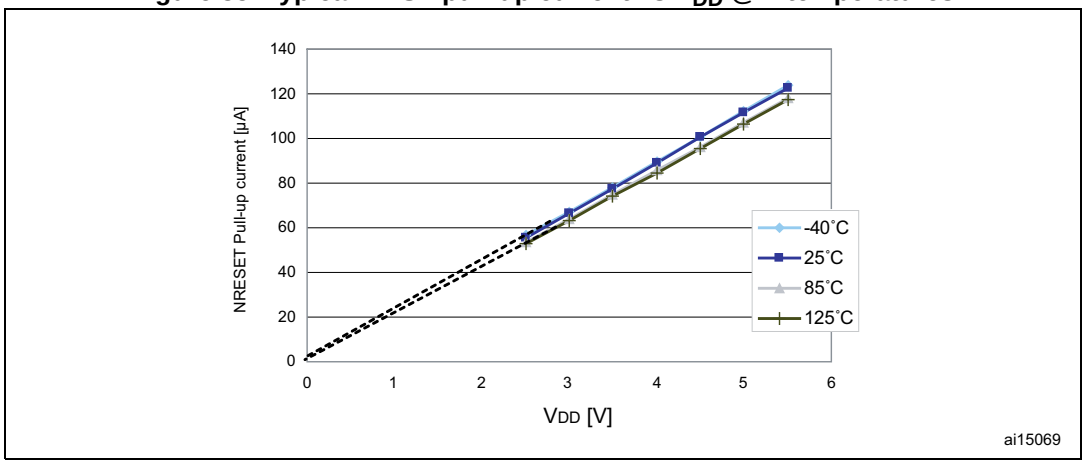
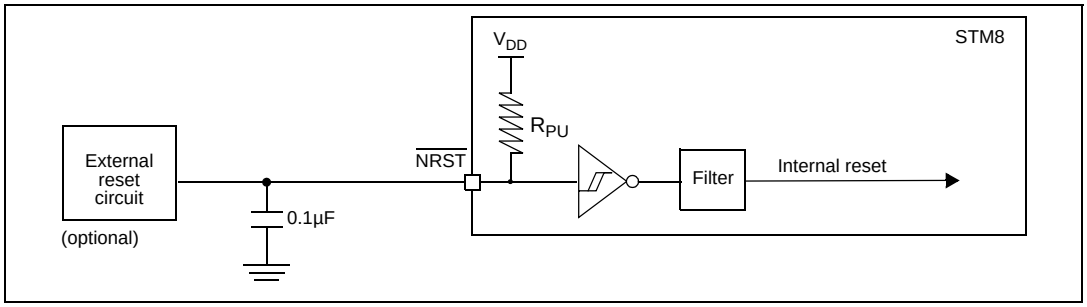


Figure 35. Typical NRST pull-up current vs V_{DD} @ 4 temperatures



The reset network shown in *Figure 36* protects the device against parasitic resets. The user must ensure that the level on the NRST pin can go below the V_{IL} max. level specified in *Table 41*. Otherwise the reset is not taken into account internally. For power consumption sensitive applications, the capacity of the external reset capacitor can be reduced to limit charge/discharge current. If the NRSTsignal is used to reset the external circuitry, care must be taken of the charge/discharge time of the external capacitor to fulfill the external device's reset timing conditions. The minimum recommended capacity is 10 nF.

Figure 36. Recommended reset pin protection



10.3.10 10-bit ADC characteristics

Subject to general operating conditions for V_{DDA}, f_{MASTER}, and T_A unless otherwise specified.

Table 44. ADC characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{ADC}	ADC clock frequency	V_{DDA} = 3 to 5.5 V	1		4	MHz
		V_{DDA} = 4.5 to 5.5 V	1		6	
V_{DDA}	Analog supply		3		5.5	V
V_{REF+}	Positive reference voltage		2.75(1)		V_{DDA}	V
V_{REF-}	Negative reference voltage		V_{SSA}		0.5(1)	V
V_{AIN}	Conversion voltage range(2)		V_{SSA}		V_{DDA}	V
		Devices with external V_{REF+}/V_{REF-} pins	V_{REF-}		V_{REF+}	V
C_{ADC}	Internal sample and hold capacitor			3		pF
t_S(2)	Sampling time	f_{ADC} = 4 MHz	0.75			µs
		f_{ADC} = 6 MHz	0.5			
t_{STAB}	Wakeup time from standby			7		µs
t_{CONV}	Total conversion time (including sampling time, 10-bit resolution)	f_{ADC} = 4 MHz	3.5			µs
		f_{ADC} = 6 MHz	2.33			µs
			14			$1/f_{ADC}$

1. Data guaranteed by design, not tested in production.
2. During the sample time the input capacitance C_{AIN} (3 pF max) can be charged/discharged by the external source. The internal resistance of the analog source must allow the capacitance to reach its final voltage level within t_S. After the end of the sample time t_S, changes of the analog input voltage have no effect on the conversion result. Values for the sample clock t_S depend on programming.

Table 45. ADC accuracy with R_{AIN} < 10 kΩ , V_{DDA} = 5 V

Symbol	Parameter	Conditions	Typ	Max(1)	Unit
$\|E_T\|$	Total unadjusted error (2)	f_{ADC} = 2 MHz	1	2.5	LSB
		f_{ADC} = 4 MHz	1.4	3	
		f_{ADC} = 6 MHz	1.6	3.5	
$\|E_O\|$	Offset error (2)	f_{ADC} = 2 MHz	0.6	2	
		f_{ADC} = 4 MHz	1.1	2.5	
		f_{ADC} = 6 MHz	1.2	2.5	
$\|E_G\|$	Gain error (2)	f_{ADC} = 2 MHz	0.2	2	
		f_{ADC} = 4 MHz	0.6	2.5	
		f_{ADC} = 6 MHz	0.8	2.5	
$\|E_D\|$	Differential linearity error (2)	f_{ADC} = 2 MHz	0.7	1.5	
		f_{ADC} = 4 MHz	0.7	1.5	
		f_{ADC} = 6 MHz	0.8	1.5	
$\|E_L\|$	Integral linearity error (2)	f_{ADC} = 2 MHz	0.6	1.5	
		f_{ADC} = 4 MHz	0.6	1.5	
		f_{ADC} = 6 MHz	0.6	1.5	

1. Data based on characterization results for LQFP80 device with V_{REF+}/V_{REF-}, not tested in production.
2. ADC accuracy vs. negative injection current: Injecting negative current on any of the analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to standard analog pins which may potentially inject negative current. Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in *Section 10.3.6* does not affect the ADC accuracy.

Table 46. ADC accuracy with R_{AIN} < 10 kΩ R_{AIN}, V_{DDA} = 3.3 V

Symbol	Parameter	Conditions	Typ	Max(1)	Unit
$\|E_T\|$	Total unadjusted error(2)	f_{ADC} = 2 MHz	1.1	2	LSB
		f_{ADC} = 4 MHz	1.6	2.5	
$\|E_O\|$	Offset error(2)	f_{ADC} = 2 MHz	0.7	1.5	
		f_{ADC} = 4 MHz	1.3	2	
$\|E_G\|$	Gain error(2)	f_{ADC} = 2 MHz	0.2	1.5	
		f_{ADC} = 4 MHz	0.5	2	
$\|E_D\|$	Differential linearity error(2)	f_{ADC} = 2 MHz	0.7	1	
		f_{ADC} = 4 MHz	0.7	1	
$\|E_L\|$	Integral linearity error(2)	f_{ADC} = 2 MHz	0.6	1.5	
		f_{ADC} = 4 MHz	0.6	1.5	

Electromagnetic interference (EMI)

Emission tests conform to the SAE IEC 61967-2 standard for test software, board layout and pin loading.

Table 48. EMI data

Symbol	Parameter	Conditions					Unit
		General conditions	Monitored frequency band	Max f_{HSE}/f_{CPU} (1)			
				8 MHz/ 8 MHz	8 MHz/ 16 MHz	8 MHz/ 24 MHz	
S_{EMI}	Peak level	V_{DD} = 5 V T_A = 25 °C LQFP80 package conforming to SAE IEC 61967-2	0.1MHz to 30 MHz	15	20	24	dBµV
			30 MHz to 130 MHz	18	21	16	
			130 MHz to 1 GHz	-1	1	4	
	SAE EMI level		SAE EMI level	2	2.5	2.5	

1. Data based on characterization results, not tested in production.

Absolute maximum ratings (electrical sensitivity)

Based on two different tests (ESD and LU) using specific measurement methods, the product is stressed in order to determine its performance in terms of electrical sensitivity. For more details, refer to the application note AN1181.

Electrostatic discharge (ESD)

Electrostatic discharges (3 positive then 3 negative pulses separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts*(n+1) supply pin). This test conforms to the JESD22-A114A/A115A standard. For more details, refer to the application note AN1181.

Table 49. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Class	Maximum value (1)	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (Human body model)	T_A = 25°C, conforming to JESD22-A114	A	2000	V
$V_{ESD(CDM)}$	Electrostatic discharge voltage (Charge device model)	T_A= 25°C, conforming to JESD22-C101	IV	1000	V

1. Data based on characterization results, not tested in production.

11.1.2 LQFP64 package information

Figure 46. LQFP64 - 64-pin 14 mm x 14 mm low-profile quad flat package outline

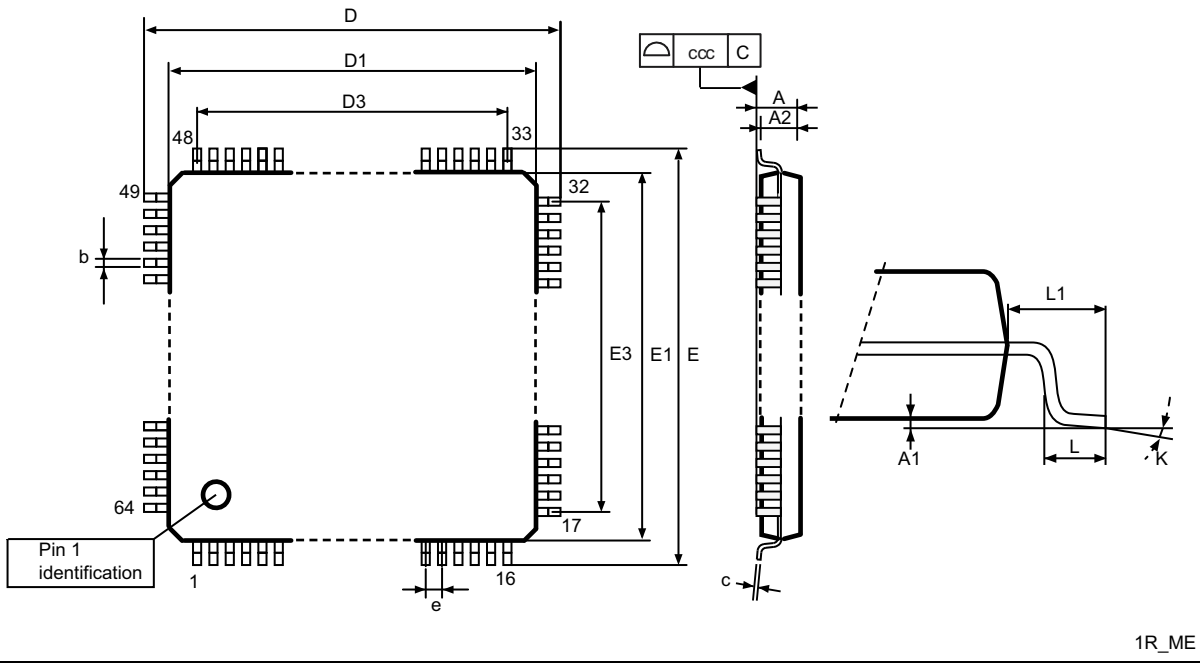
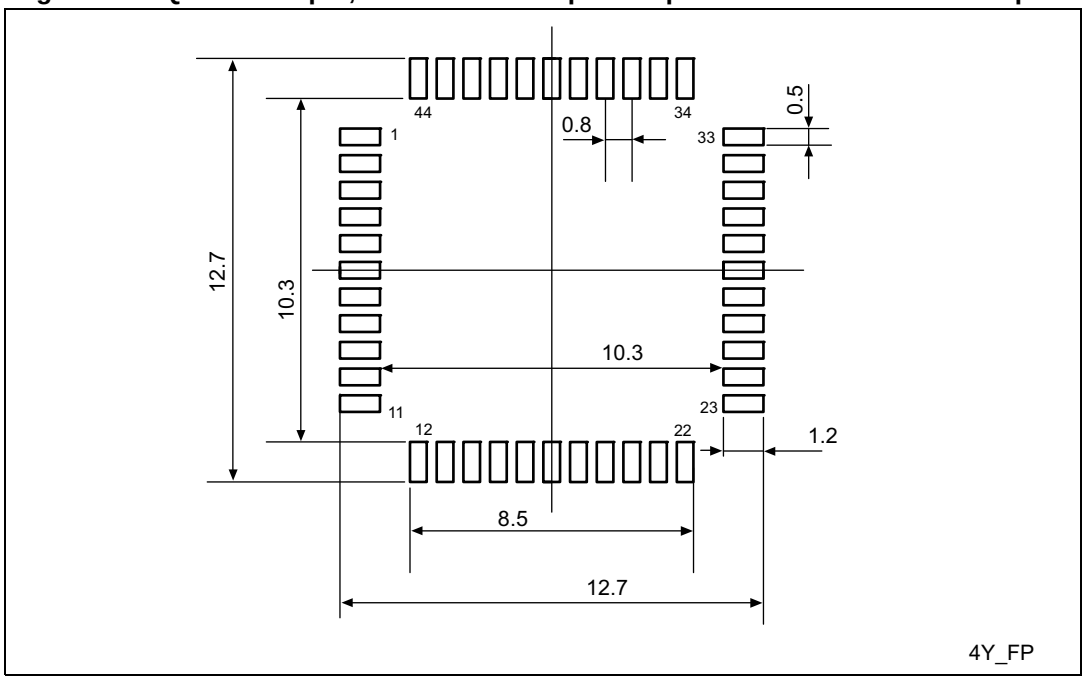


Table 52. LQFP64 - 64-pin, 14 x 14 mm low-profile quad flat package mechanical data

Symbol	mm			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A			1.600			0.0630
A1	0.050		0.150	0.0020		0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.300	0.370	0.450	0.0118	0.0146	0.0177
C	0.090		0.200	0.0035		0.0079
D	15.800	16.000	16.200	0.6220	0.6299	0.6378
D1	13.800	14.000	14.200	0.5433	0.5512	0.5591
D3		12.000			0.4724	
E	15.800	16.000	16.200	0.6220	0.6299	0.6378
E1	13.800	14.000	14.200	0.5433	0.5512	0.5591
E3		12.000			0.4724	
e		0.800			0.0315	
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1		1.000			0.0394	

Figure 54. LQFP44 - 44-pin, 10 x 10 mm low-profile quad flat recommended footprint

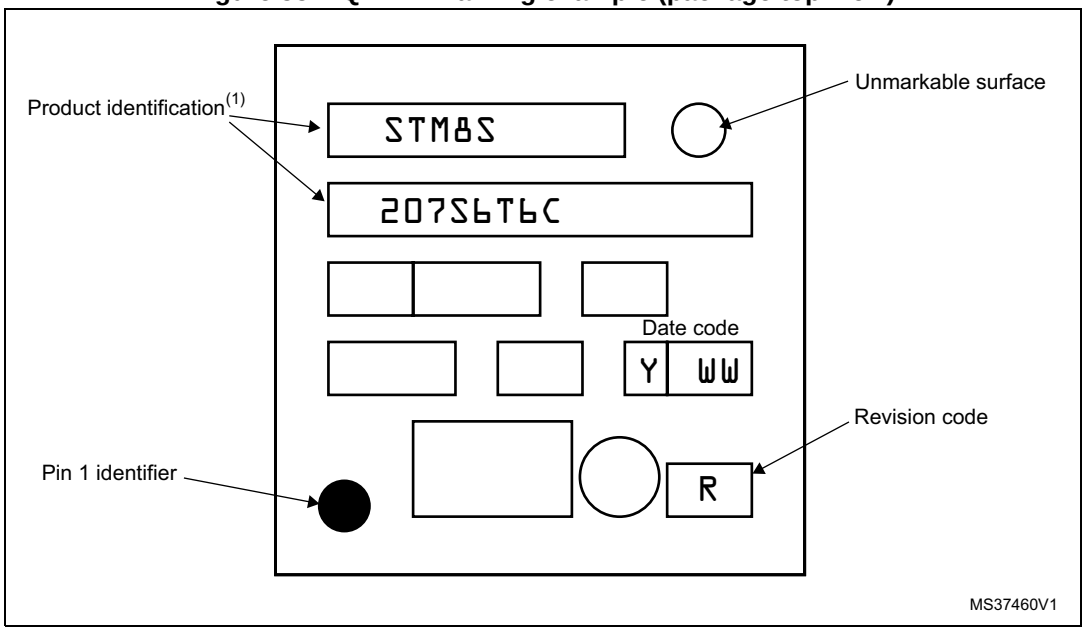


1. Dimensions are expressed in millimeters.

Device marking

The following figure shows the marking for the LQFP44 package.

Figure 55. LQFP44 marking example (package top view)



1. Parts marked as “ES”,”E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

14 Revision history

Table 58. Document revision history

Date	Revision	Changes
23-May-2008	1	Initial release.
05-Jun-2008	2	Added part numbers on page 1 and in *Table 2 on page 11*. Updated *Section 4: Product overview*. Updated *Section 10: Electrical characteristics*.
22-Jun-2008	3	Added part numbers on page 1 and in *Table 2 on page 11*.
12-Aug-2008	4	Added 32 pin device pinout and ordering information. Updated UBC option description in *Table 13 on page 48*. USART renamed UART1, LINUART renamed UART3. Max. ADC frequency increased to 6 MHz.
20-Oct-2008	5	Removed STM8S207K4 part number. Removed LQFP64 14 x 14 mm package. Added medium and high density Flash memory categories. Added *Section 6: Memory and register map on page 34*. Replaced beCAN3 by beCAN in *Section 4.14.5: beCAN*. Updated *Section 10: Electrical characteristics on page 52*. Updated LQFP44 (*Figure 53* and *Table 55*), and LQFP32 outline and mechanical data (*Figure 56*, and *Table 56*).
08-Dec-2008	6	Changed V_{DD} minimum value from 3.0 to 2.95 V. Updated number of High Sink I/Os in pinout. Removed FLASH _NFPR and FLASH _FPR registers in *Table 9: General hardware register map*.
30-Jan-2009	7	Removed preliminary status. Removed VQFN32 package. Added STM8S207C6, STM8S207S6. Updated external interrupts in *Table 2 on page 11*. Updated *Section 10: Electrical characteristics*.
10-Jul-2009	8	Document status changed from “preliminary data” to “datasheet”. Added LQFP64 14 x 14 mm package. Added STM8S207M8, STM8S207SB, STM8S208R8, STM8S208R6, STM8S208C8, and STM8S208C6, STM8S208SB, STM8S208S8, and STM8S208S6. Replaced “CAN” with “beCAN”. Added *Table 3* to *Section 4.5: Clock controller*. Updated *Section 4.8: Auto wakeup counter*. Added beCAN peripheral (impacting *Table 1* and *Figure 6*). Added footnote about CAN_RX/TX to pinout figures *5*, *4*, and *6*. *Table 6*: Removed ‘X’ from wpu column of I^2C pins (no wpu available). Added *Table 11: Interrupt mapping*.

Table 58. Document revision history (continued)

Date	Revision	Changes
18-Feb-2015	13	Updated: – *Figure 43: LQFP80 - 80-pin, 14 x 14 mm low-profile quad flat package outline* – *Table 51: LQFP80 - 80-pin, 14 x 14 mm low-profile quad flat package mechanical data* – *Figure 51: LQFP80 - 80-pin, 14 x 14 mm low-profile quad flat package mechanical data* – *Figure 47: LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat package outline* – *Table 53: LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat package mechanical data* – *Figure 50: LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat package outline* – *Table 54: LQFP48 - 48-pin, 7x 7 mm low-profile quad flat package mechanical* – *Figure 56: LQFP32 - 32-pin, 7 x 7 mm low-profile quad flat package outline* – *Table 56: LQFP32 - 32-pin, 7 x 7 mm low-profile quad flat package mechanical data* Added: – *Figure 44: LQFP80 recommended footprint* – *Figure 45: LQFP80 marking example (package top view)* – *Figure 48: LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat recommended footprint* – *Figure 49: LQFP64 marking example (package top view)* – *Figure 51: LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat recommended footprint* – *Figure 52: LQFP48 marking example (package top view)* – *Figure 54: LQFP44 - 44-pin, 10 x 10 mm low-profile quad flat recommended footprint* – *Figure 55: LQFP44 marking example (package top view)* – *Figure 57: LQFP32 - 32-pin, 7 x 7 mm low-profile quad flat recommended footprint* – *Figure 58: LQFP32 marking example (package top view)*